SEMICONDUTTORI

Si **Ge** ~ 90°C

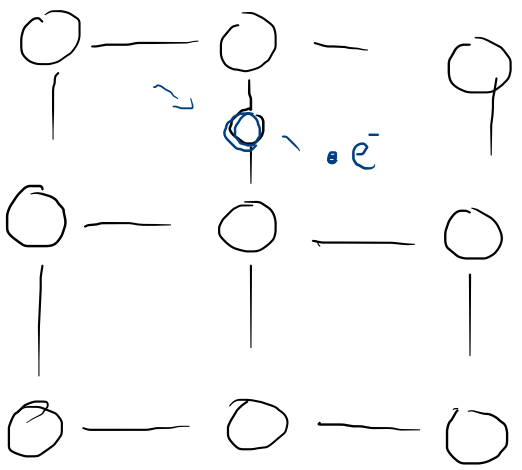
L 200°C

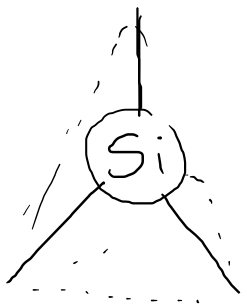
GaAs

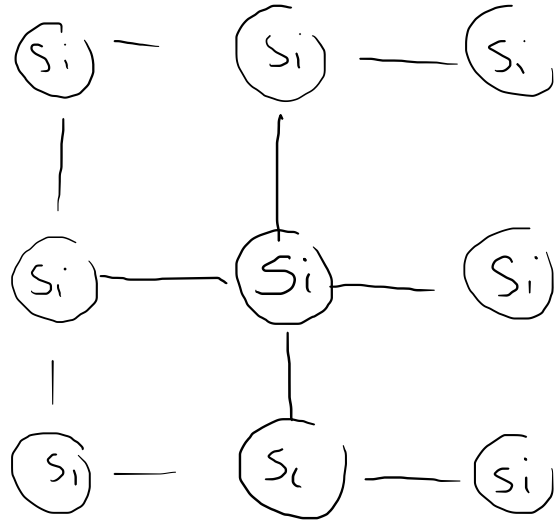
Si 1h e^-

28 — 1hp

— 1hn







$\mu_e >> \mu_L$

MU

$\mu_{Si_e} = 1500 \left[\frac{cm^2}{V \cdot s}\right]$

$\mu_{Si_L} \cong 475$

$n_i(T) \equiv P_{i(T)} \cong 1{,}5 \cdot 10^{10} \left[\frac{1}{cm^3}\right]$

$5 \cdot 10^{22}$

PURO o INTRINSECO

$$\sigma_{Si} = n_i \, q \, \mu_n + p_i \cdot q \cdot \mu_p$$